

L Number	Hits	Search Text	DB	Time stamp
1	136444	gate with (dielectric insulat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:26
2	13824	(ozone oxygen) near2 radical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:35
3	5803887	@ad>19990428 @RLAD>19990428	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:35
4	4433	(oxidation oxidating oxidizing oxidization) same (nitriding nitridating nitridation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:59
5	138283	silicon with nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:35
6	4489	post with anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:35
7	28	((oxidation oxidating oxidizing oxidization) same (nitriding nitridating nitridation)) same (post with anneal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:36
8	25	(gate with (dielectric insulat\$3)) same ((ozone oxygen) near2 radical) same (oxidation oxidating oxidizing oxidization)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 09:59
9	47	(((gate with (dielectric insulat\$3)) same ((oxidation oxidating oxidizing oxidization) same (nitriding nitridating nitridation))) same (silicon with nitride)) not (@ad>19990428 @RLAD>19990428)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/28 10:08